Electronic Supplementary Material (ESI) for Nanoscale.
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Supporting information

Highly Flexible and Degradable Memory Electronics Comprised of All-Biocompatible Materials

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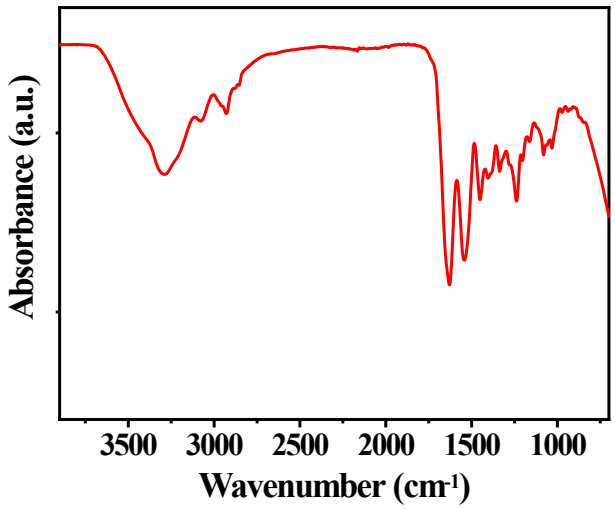

Figure S1. FTIR spectrum of the gelatin film.

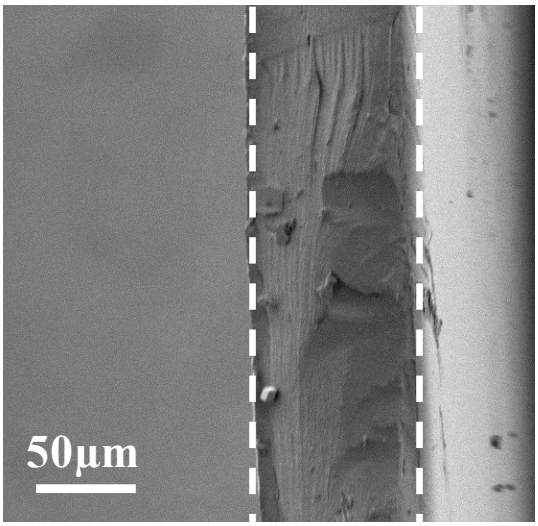

Figure S2. The Cross-sectional scanning electron microscopy (SEM) image of gelatin substrate.

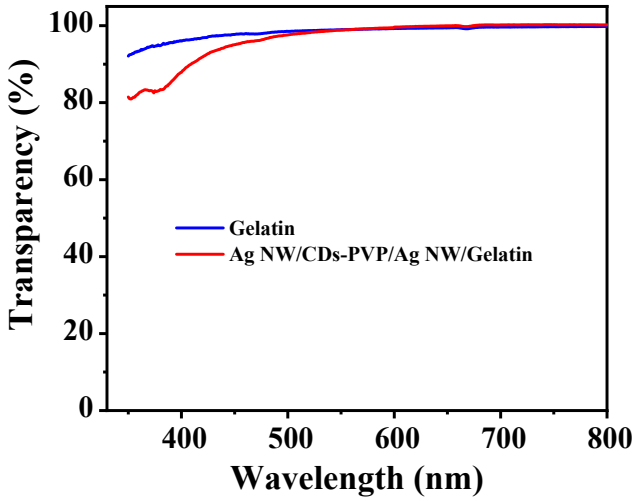

Figure S3. Optical transmittance of pure gelatin substrate and Ag NW/CDs-PVP/Ag NW/Gelatin film.

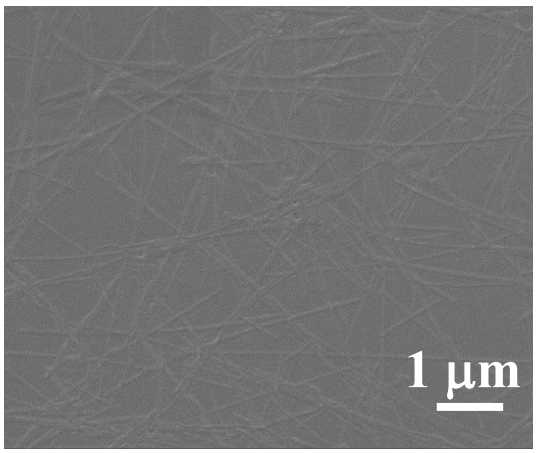

Figure S4. SEM micrograph of Ag NW-gelatin electrode.

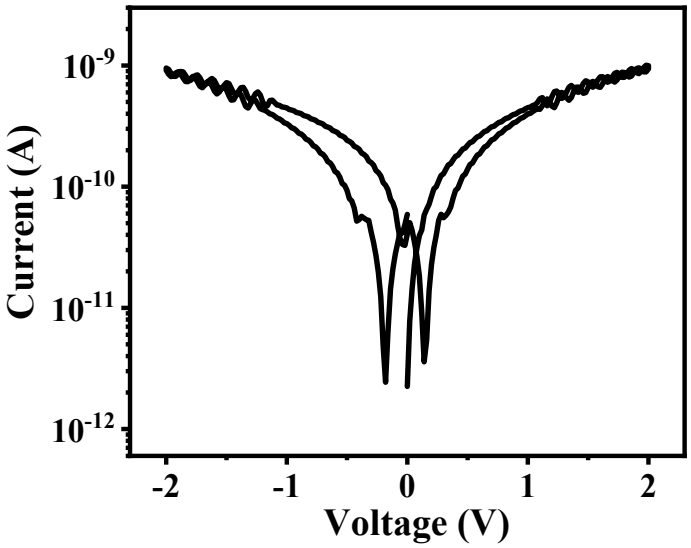

Figure S5. Current versus voltage (*I-V*) curve of memory with an architecture of Ag NW/PVP/Ag NW/Gelatin.

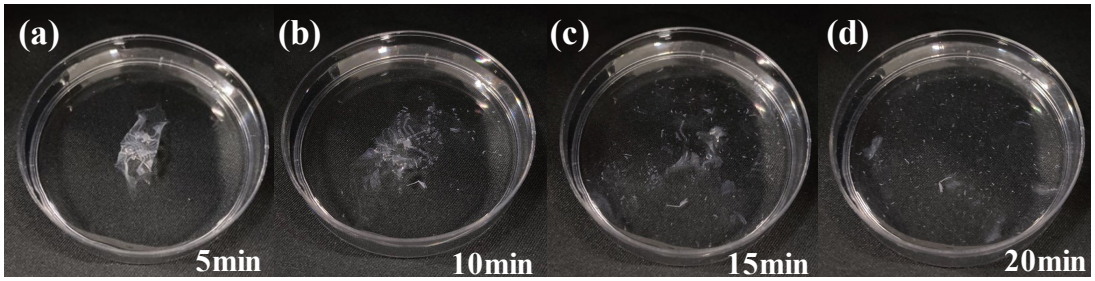

Figure S6. Dissolution process of the memory device in deionized water at room temperature.